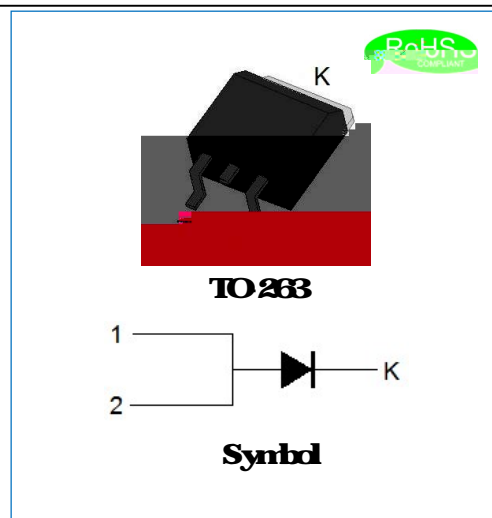




- ✦ TrenchMOS barrierschottky technology
- ✦ Lowstored charge majority carrier conduction
- ✦ Ultra low forward voltage drop
- ✦ Lowleakage current
- ✦ Lowpower loss and high efficiency
- ✦ High forward surge capacity

- ✦ Case: TO 263 molded plastic
- ✦ Terminals: Solder plated, solderable per J-STD 002



(Rating at 25 °C ambient temperature unless otherwise specified)

Parameter	Symbol	Value	Unit
Maximum repetitive peak reverse voltage	V_{RRM}	45	V
Maximum RMS voltage	V_{RMS}	31.5	V
Maximum DC blocking voltage	V_{DC}	45	V
Average forward current	$I_{F(AV)}$	30	A
Peak forward surge current: 83ms single half sine wave superimposed on rated load	I_{FSM}	290	A
Operating junction temperature range	T_j	-55 to +150	
Storage temperature range	T_{stg}	-55 to +150	

(Rating at 25 °C ambient temperature unless otherwise specified)

Parameter	Conditions	Symbol	Value	Value	Unit	
Forward voltage	$I_F=0.5A, T_A=25$	V_F	-	0.32	V	
	$I_F=1.5A, T_A=25$		-	0.45		
	$I_F=2.0A, T_A=25$		-	0.47		
	$I_F=3.0A, T_A=25$		-	0.49		0.56
Reverse current	$V_R=45V, T_A=25$	I_R	-	-	100	μA
	$V_R=45V, T_A=125$		-	-	50	mA
Reverse recovery time	$I_F=3A, di/dt=100A/\mu s$	t_r	-	-	30	ns
Junction capacitance	$V_R=5V_{DC}, f=1MHz$	C_j	-	750	-	pF



R_{th(j-c)}	Thermal resistances from junction to case	21	°W

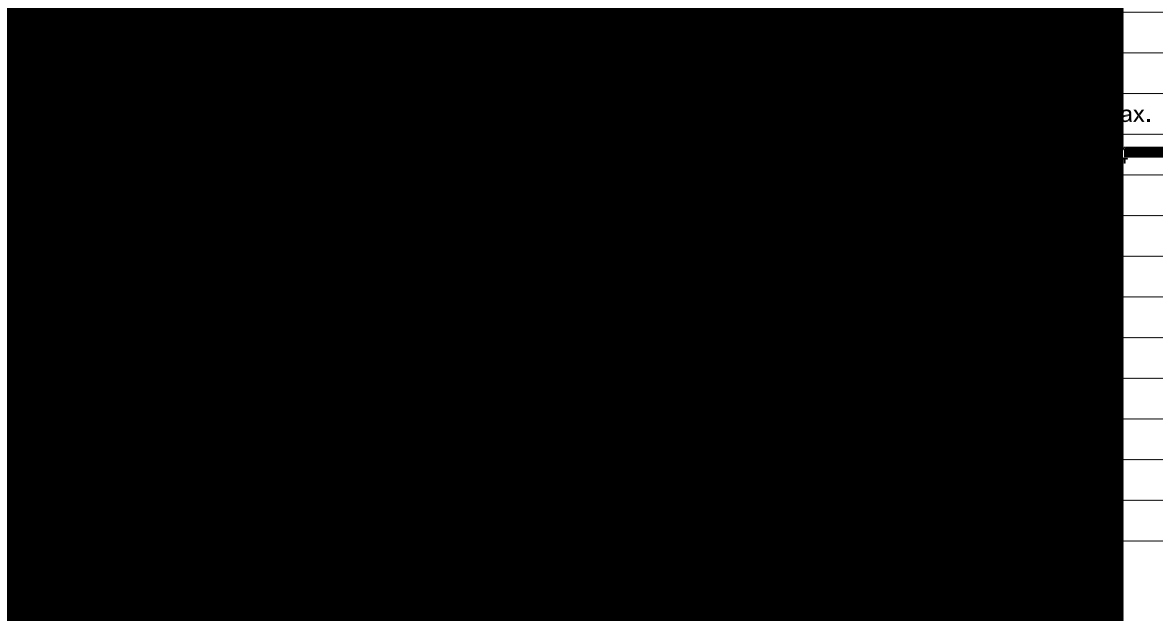
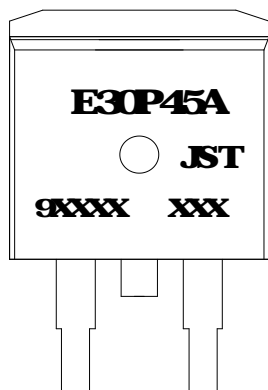




FIG. 1: Typical forward characteristics(25)

FIG. 2 Typical reverse characteristics(25)

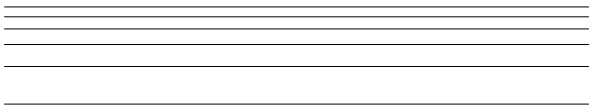




FIG.5 Typical transient thermal impedance

FIG.6 Typical junction capacitance

